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Complete if Known	
Application Number	
Filing Date	
First Named Inventor	**Dingjun Wu, et al.**
Art Unit	
Examiner Name	
Attorney Docket Number	**06469 USA**

Sheet **1** of **2**

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US- 2001/0011526 A1	8/9/2001	K. Doering, et al.	
		US- 2001/0055852 A1	12/27/2001	T. S. Moise, et al.	
		US- 5,288,662	2/24/1994	A. Lagendijk, et al.	
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Examiner Initials*	Cite No.[1]	Foreign Patent Document Country Code[3] Number[4] Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
		EP 1 001 459 A2	5/17/2000	Europe		✓
		WO 00/40772	7/13/2000	World		✓
		WO 00/79019 A1	12/28/2000	World		✓
		WO 02/43114 A2	5/30/2002	World		✓
		WO 02/43115 A2	5/30/2002	World		✓

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Sheet **2** of **2**

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
MSR 9/22/04		K. K. Shih, "Hafnium Dioxide Etch-Stop Layer for Phase-Shifting Masks," J. Vac. Sci. Technol. B 11(6), pp. 2130-2131(1993).	✓
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